

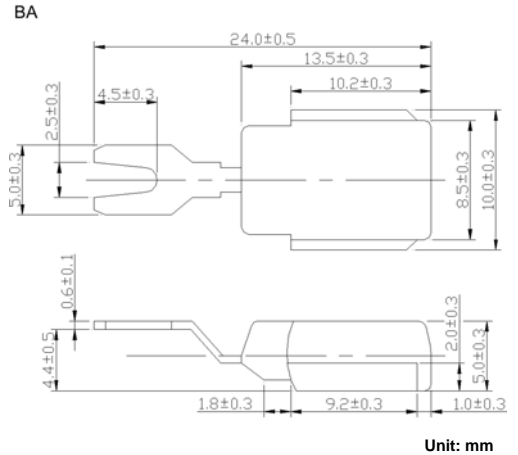
## Technical Specification:

### Features:

- ◆ High power capability
- ◆ Economical
- ◆ Avalanche Voltage: 24V to 32V

### Mechanical Data:

- ◆ Copper cup with transfer molded plastic
- ◆ Epoxy: UL94-0 rate flame retardant
- ◆ Polarity: GBA50-P lead-P  
GBA50-N lead-N
- ◆ Glass passivated chip
- ◆ Technology vacuum soldered
- ◆ Lead: Plated lead, solderable per MIL-STD-202E method 208C
- ◆ Weight: 0.094 ounces, 2.65 grams



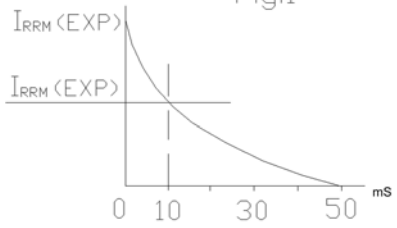
## Maximum Ratings and Electrical Characteristics

- ◆ Rating at 25°C ambient temperature unless otherwise specified.
- ◆ Single phase, half wave, 60Hz, resistive or inductive load.
- ◆ For capacitive load derate current by 20%.

Parameters	Symbols	GBA50-P /GBA50-N			Units
		Min.	Nominal	Max.	
DC peak repetitive reverse voltage	$V_{RRM}$		20		Volts
Working peak reverse voltage	$V_{RWM}$		20		
DC blocking voltage	$V_R$		20		
Average rectified forward current at $T_c=125^\circ\text{C}$	$I_T$		50		Amps
Repetitive peak reverse surge current $T_r=10\text{m sec duty cycle } <1\%$	$I_{TSM}$		50		Amps
Breakdown voltage ( $V_{BR}$ @ $I_F=100\text{mA}$ ) $I_F=90\text{Amps}, T_c=150^\circ\text{C}, PW=80\text{usec}$	$V_{BR}$ $V_{BR}$	24	25/27	32 40	Volts
Forward voltage drop ( $V_{sd}$ ) @ $I_F=100\text{Amps} <300\text{usec}$	$V_F$	0.98	1.05	1.08	Volts
Peak forward surge current	$I_{FSM}$		600		Amps
Reverse leakage ( $I_R=20\text{Vdc}$ ) $T_A=25^\circ\text{C}$	$I_R$	0.2	1.0	2.0	$\mu\text{A}$
Operating and storage junction temperature range	$T_J, T_{STG}$	-65 to +175			$^\circ\text{C}$

Notes: 1. Enough heatsink must be considered in application.

Fig.1



Surge current characteristics